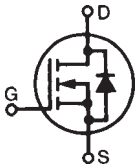
IXYS

Polar3™ HiPerFET™ Power MOSFET

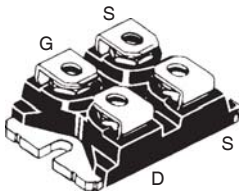
IXFN110N60P3

V_{DSS}	=	600V
I_{D25}	=	90A
$R_{DS(on)}$	≤	56mΩ
t_{rr}	≤	250ns

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Rectifier



miniBLOC
E153432



G = Gate D = Drain
S = Source

Either Source Terminal S can be used as the Source Terminal or the Kelvin Source (Gate Return) Terminal.

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	600	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	600	V
V_{GSS}	Continuous	±30	V
V_{GSM}	Transient	±40	V
I_{D25}	T_C = 25°C	90	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	275	A
I_A	T_C = 25°C	55	A
E_{AS}	T_C = 25°C	3	J
dv/dt	$I_S \le I_{DM}$, $V_{DD} \le V_{DSS}$, $T_J \le$ 150°C	35	V/ns
P_D	T_C = 25°C	1500	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
V_{ISOL}	50/60 Hz, RMS, t = 1minute	2500	V~
	$I_{ISOL} \le$ 1mA, t = 1s	3000	V~
M_d	Mounting Torque for Base Plate	1.5/13	Nm/lb.in
	Terminal Connection Torque	1.3/11.5	Nm/lb.in
Weight		30	g

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 3mA	600			V
$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 8mA	3.0		5.0	V
I_{GSS}	V_{GS} = ±30V, V_{DS} = 0V			±200	nA
I_{DSS}	V_{DS} = V_{DSS}, V_{GS} = 0V			50	μA
	T_J = 125°C			2.75	mA
$R_{DS(on)}$	V_{GS} = 10V, I_D = 55A, Note 1			56	mΩ

Features

- International Standard Package
- miniBLOC with Aluminum Nitride Isolation
- Avalanche Rated
- Low Package Inductance
- Fast Intrinsic Rectifier
- Low $R_{DS(on)}$ and Q_G

Advantages

- Easy to Mount
- Space Savings

Applications

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- Uninterrupted Power Supplies
- AC Motor Drives
- High Speed Power Switching Applications

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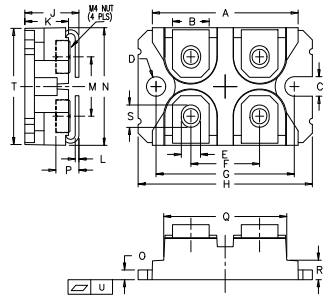
Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = 20V, I_D = 55A, Note 1	65	105		S
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		18		nF
C_{oss}			1550		pF
C_{rss}			8		pF
R_{Gi}	Gate Input Resistance		1.2		Ω
$t_{d(on)}$	**Resistive Switching Times** V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 55A, R_G = 1Ω (External)		63		ns
t_r			30		ns
$t_{d(off)}$			106		ns
t_f			15		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 55A		254		nC
Q_{gs}			80		nC
Q_{gd}			68		nC
R_{thJC}				0.083	°C/W
R_{thCS}			0.05		°C/W

SOT-227B (IXFN) Outline



(M4 screws (4x) supplied)

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0V			110	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			440	A
V_{SD}	I_F = 100A, V_{GS} = 0V, Note 1			1.5	V
t_{rr}	I_F = 55A, -di/dt = 100A/μs, V_R = 100V, V_{GS} = 0V			250	ns
Q_{RM}			1.6		μC
I_{RM}			14.0		A

Note 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2 4,860,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

Fig. 1. Output Characteristics @ T_J = 25ºC

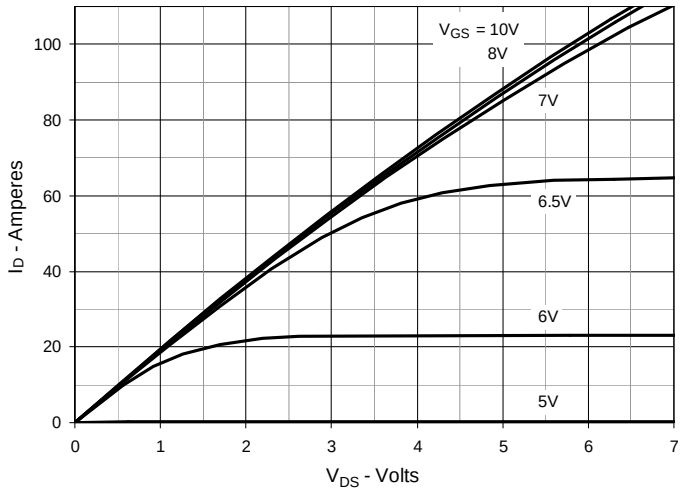


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

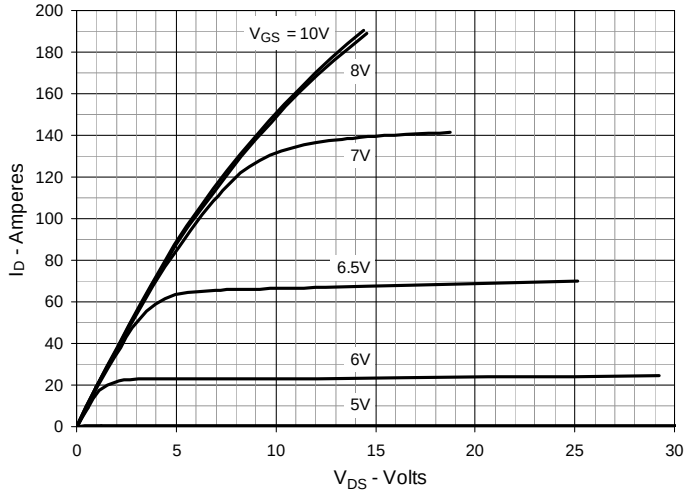


Fig. 3. Output Characteristics @ T_J = 125ºC

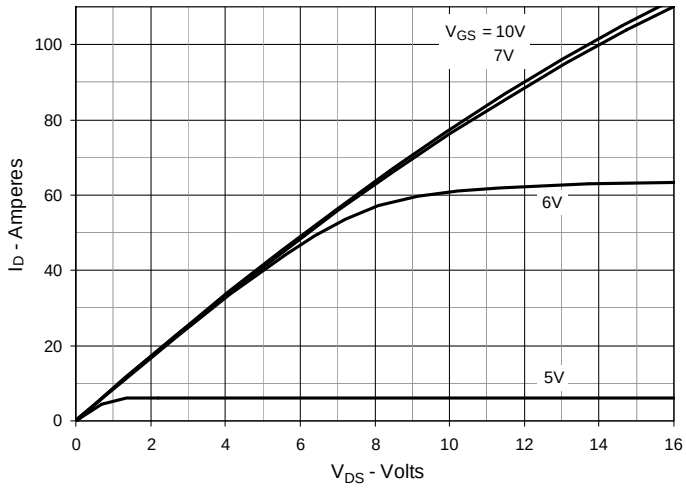


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 55A Value vs. Junction Temperature

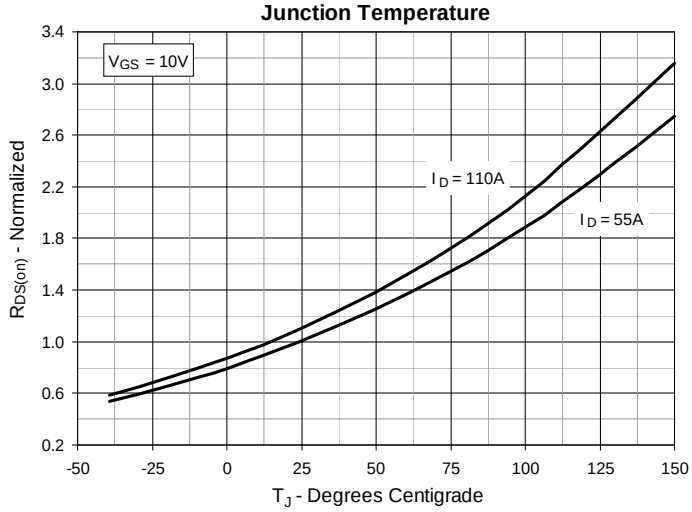


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 55A Value vs. Drain Current

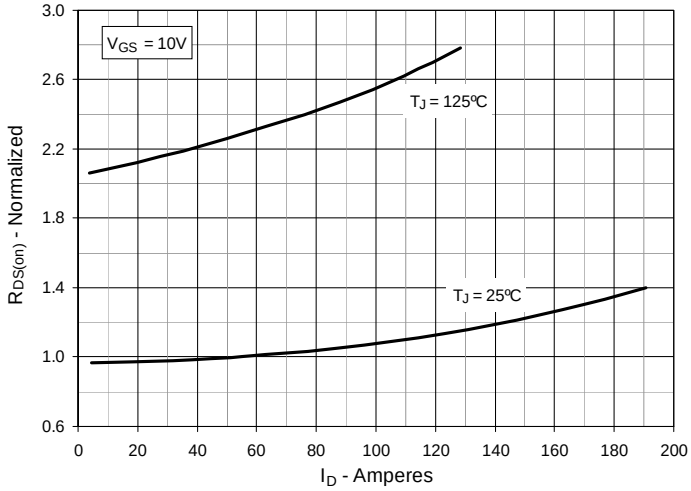


Fig. 6. Maximum Drain Current vs. Case Temperature

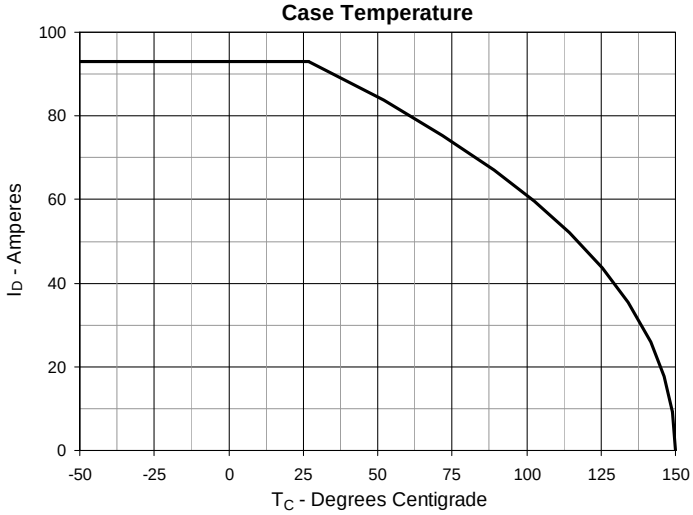


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Fig. 7. Input Admittance

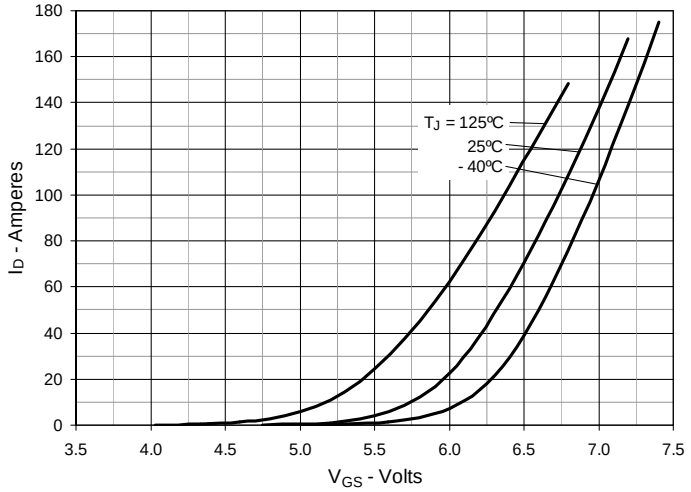

Fig. 8. Transconductance

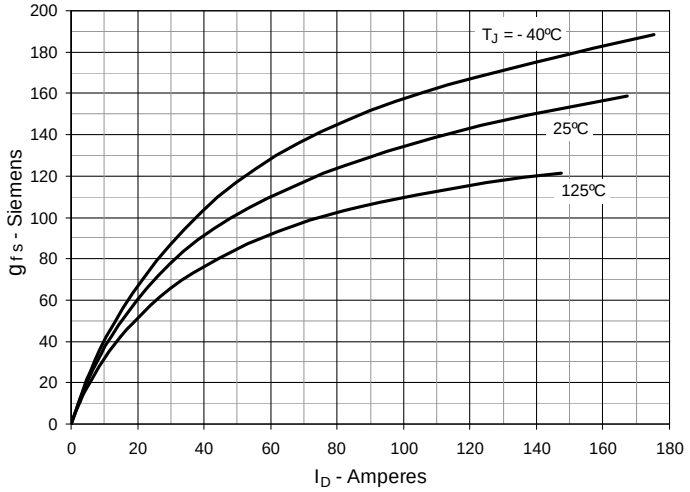

Fig. 9. Forward Voltage Drop of Intrinsic Diode

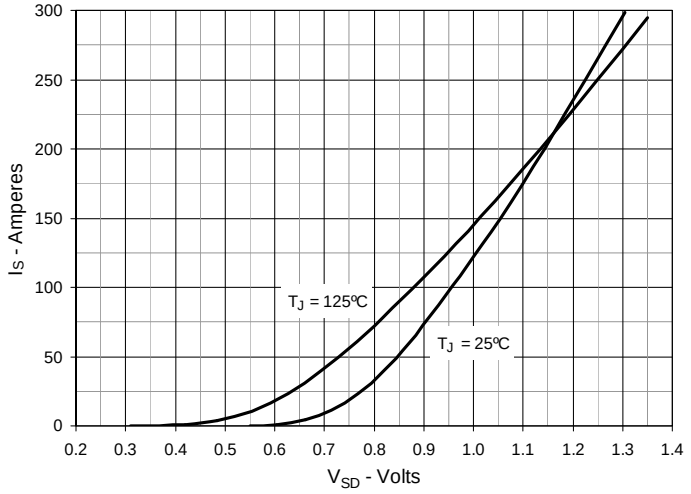

Fig. 10. Gate Charge

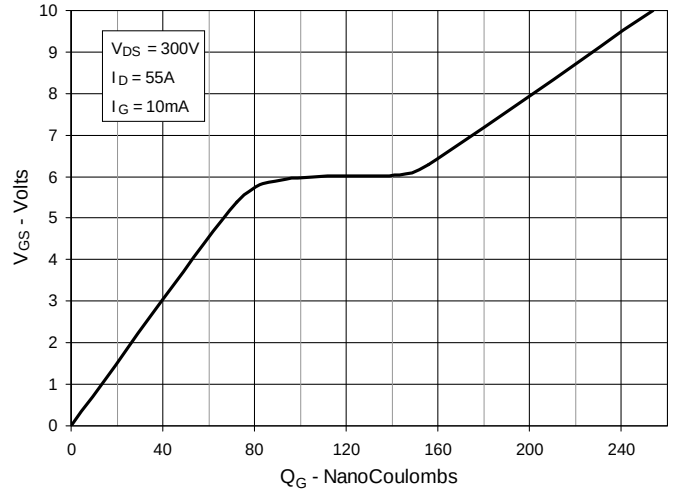

Fig. 11. Capacitance

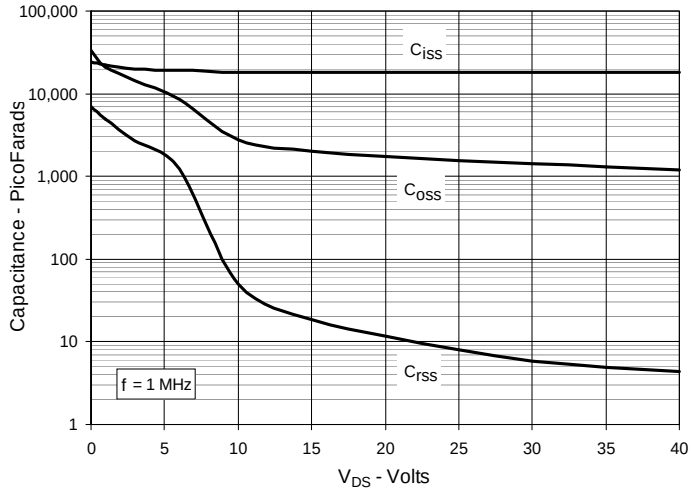

Fig. 12. Forward-Bias Safe Operating Area

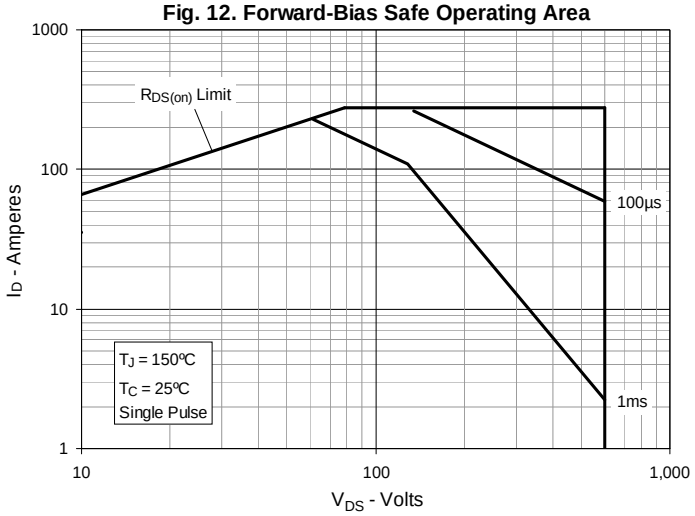

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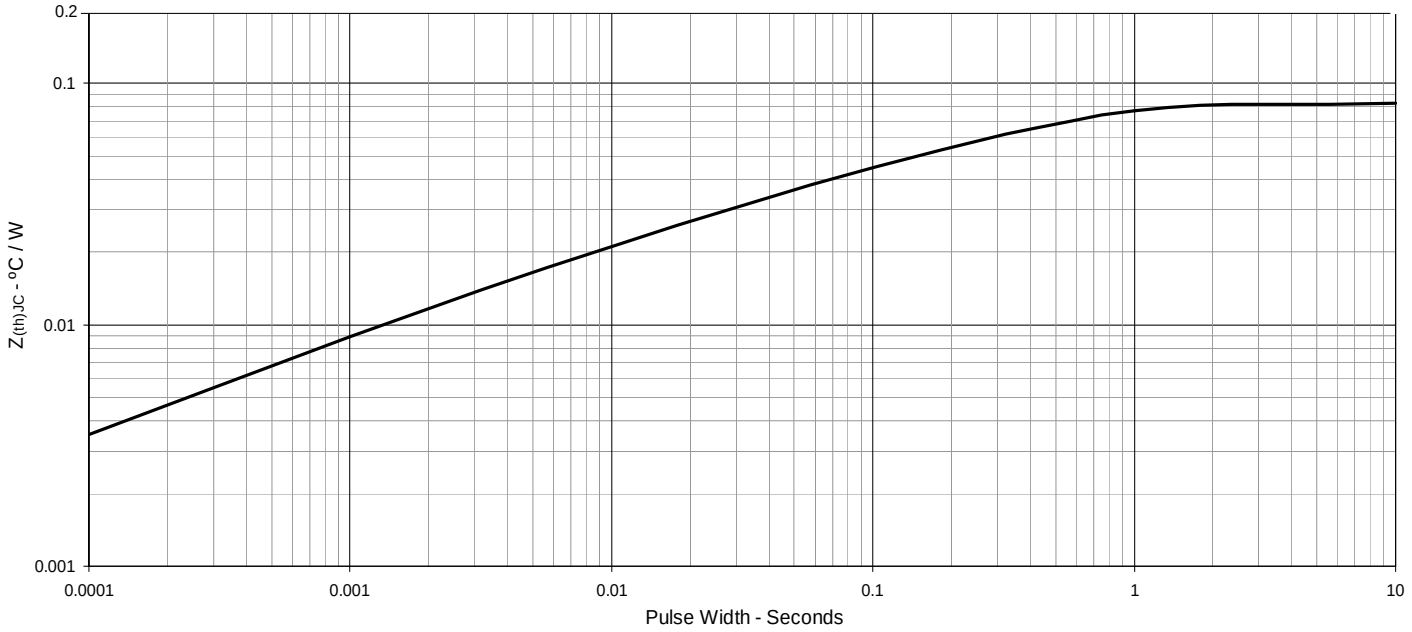
Fig. 13. Maximum Transient Thermal Impedance



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